

Table of contents

Semiconductor Quantum Structures

Subvolume C3: Optical Properties (Part 3)

(edited by E. KASPER and C. KLINGSHIRN)

3	Group IV semiconductors	1
3.1	Basic properties, growth and preparation methods of group IV heterostructures (by E. KASPER)	1
3.1.1	Epitaxial growth processes	4
3.1.2	Lattice mismatch and its implication on critical thickness and interface structure	13
3.1.3	Virtual substrates and strain relaxation	17
3.1.4	References for 3.1	18
3.2	Influence of strain on bandstructure (by E. KASPER)	19
3.2.1	Hydrostatic strain	19
3.2.2	Uniaxial strain	20
3.2.3	Band alignment of strained SiGe	22
3.2.3.1	Average valence band energy	22
3.2.3.2	Compressive strain	23
3.2.3.3	Tensile strain	24
3.2.4	References for 3.2	25
3.3	Single and coupled quantum wells: SiGe (by N. USAMI and Y. SHIRAKI)	26
3.3.1	Introduction	26
3.3.2	Photoluminescence from SiGe/Si quantum wells: Spectral features	27
3.3.3	Excitation power dependence of photoluminescence	28
3.3.4	Temperature dependence of photoluminescence	29
3.3.5	Quantum confinement effect	30
3.3.6	Effect of post-growth annealing	31
3.3.7	Effect of electric field	32
3.3.8	Effect of external stress	33
3.3.9	Fermi-edge singularity	34
3.3.10	Time-resolved photoluminescence	35
3.3.11	Growth mode transition	36
3.3.12	Type-II strained Si quantum well	38
3.3.13	Coupled quantum wells	38
3.3.14	Electroluminescence	40
3.3.15	Interband absorption	40
3.3.16	Intraband absorption	41
3.3.17	Second-harmonic generation	44
3.3.18	Phonon modes	44
3.3.19	Cyclotron resonance	46
3.3.20	References for 3.3	47

3.4	Optical properties of Si/Ge superlattices (by G. THEODOROU and E. KASPER)	50
3.4.1	Introduction.	50
3.4.2	The empirical tight-binding model	51
3.4.2.1	Uniaxial strain along the [001] direction	51
3.4.2.2	Uniaxial strain along the [111] direction	53
3.4.2.3	Optical properties.	53
3.4.3	Si/Ge SLs grown along the [001] direction	53
3.4.3.1	Electronic properties	53
3.4.3.2	Optical properties.	55
3.4.3.3	Interface intermixing	59
3.4.4	Si/Ge SLs grown along the [111] direction	61
3.4.5	Raman spectroscopy	64
3.4.5.1	Zone-folded acoustic phonons	64
3.4.5.2	Confined optical modes and interface modes	67
3.4.6	Photoluminescence (PL)	68
3.4.6.1	Effect of hydrostatic pressure on the PL	72
3.4.7	Electroluminescence (EL)	74
3.4.8	Photoconductivity (PC) and optical Junction Space Charge Techniques (JSCT)	74
3.4.8.1	Wannier-Stark localization	77
3.4.9	Spectroscopic ellipsometry	77
3.4.10	Piezoreflectance and electroreflectance	79
3.4.11	Second-harmonic generation	81
3.4.12	Quantum dot superlattices (QDSL)	82
3.4.13	Conclusions.	84
3.4.13	References for 3.4	86
3.5	Si, Ge, and SiGe quantum wires and quantum dots (by T.P. PEARSALL)	89
3.5.1	Introduction.	89
3.5.2	Silicon and germanium quantum-wire quantum-dot structures	92
3.5.3	Synthesis of quantum wires and quantum dots	94
3.5.3.1	Self-organized epitaxy of quantum dots	94
3.5.3.2	Lithographic definition of quantum structures	99
3.5.3.3	Synthesis of free-standing Si quantum dots.	101
3.5.3.4	Photoluminescence properties of Si nanoclusters	103
3.5.3.5	Si quantum dots formed by controlled segregation of excess Si in SiO ₂ .	103
3.5.3.6	Si quantum dots formed by the controlled segregation of excess Si in SiN _x	107
3.5.4	Applications of SiGe quantum-dot structures	108
3.5.4.1	SiGe quantum-dot photodetectors	108
3.5.4.2	Si quantum-dot light-emitting diodes	111
3.5.4.3	Er-doped Si-SiO ₂ nanocluster optical amplification	114
3.5.4.4	Si quantum-dot memories	115
3.5.5	Conclusions.	116
3.5.6	References for 3.5	118
3.6	Luminescence and related properties of nanocrystalline porous silicon (by N. KOSHIDA)	121
3.6.1	Introduction.	121
3.6.2	An overview of nanostructured silicon	121
3.6.3	Fabrication technology.	122
3.6.3.2	Dry-processed silicon nanocrystallites	123
3.6.4	Nanocrystalline porous silicon.	124
3.6.4.1	Properties as a confined system	124

3.6.4.2	Photoluminescence	126
3.6.4.3	Electroluminescent devices	127
3.6.4.4	Related functions	128
3.6.4.4.1	Carrier charging effects	128
3.6.4.4.2	Ballistic transport and emission	129
3.6.4.4.3	Thermally induced acoustic emission	131
3.6.4.5	Toward monolithic functional integration.	132
3.6.5	Conclusions	133
3.6.6	References for 3.6	134

Optical Properties 3

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